

Trench MOS Barrier Schottky Rectifier

TO-220AB
TSR10L100CT



ITO-220AB
TSR10L100CTF

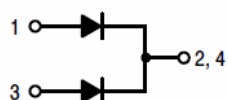


Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors



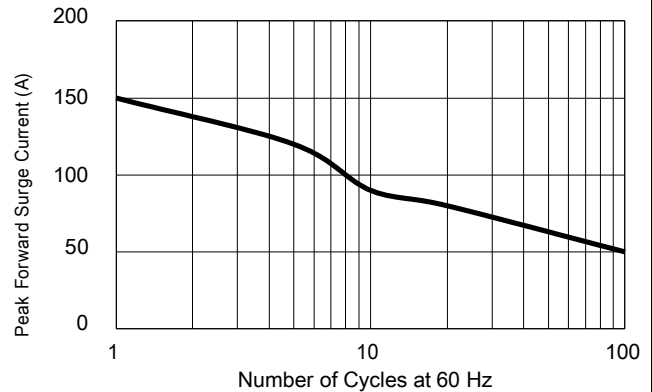
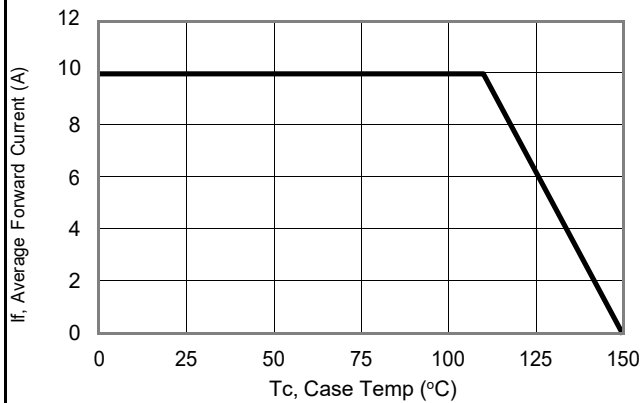
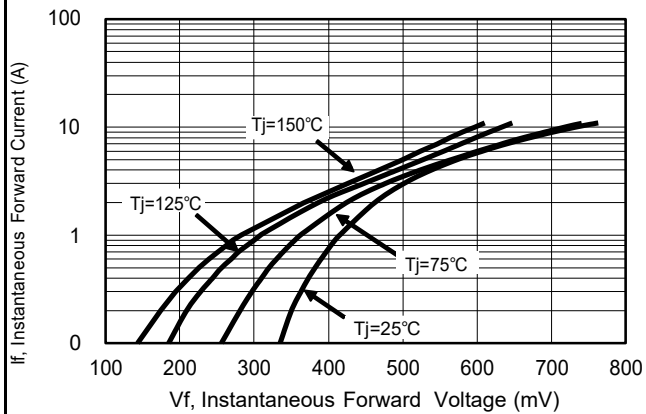
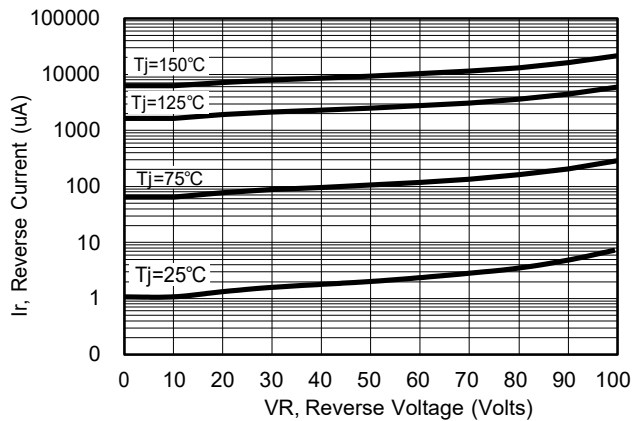
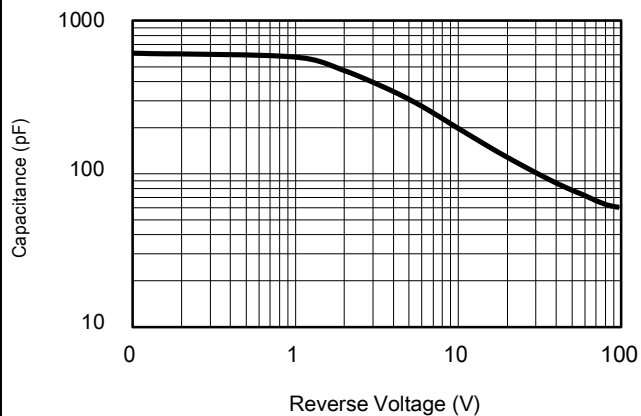
Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage			V _{RRM}	100		V
Maximum average forward rectified current			I _{F(AV)}	10		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode			I _{FSM}	160		A
Operating junction and storage temperature range			T _J , T _{STG}	-40 to +150		°C
Typical thermal resistance per diode (Mounted on FR-4 PCB)			R _{θJC}	22		°C/W
Instantaneous forward voltage			V _{F(1)}	TYP.	MAX.	V
	I _F =2A	T _J =25°C		0.44	-	
	I _F =2A	T _J =125°C		0.39	-	
	I _F =10A	T _J =25°C		0.63	0.70	
	I _F =10A	T _J =125°C		0.58	-	
Instantaneous reverse current per diode at rated reverse voltage		T _J =25°C	I _{R(2)}	-	60	uA
		T _J =125°C		-	40	mA

Notes:

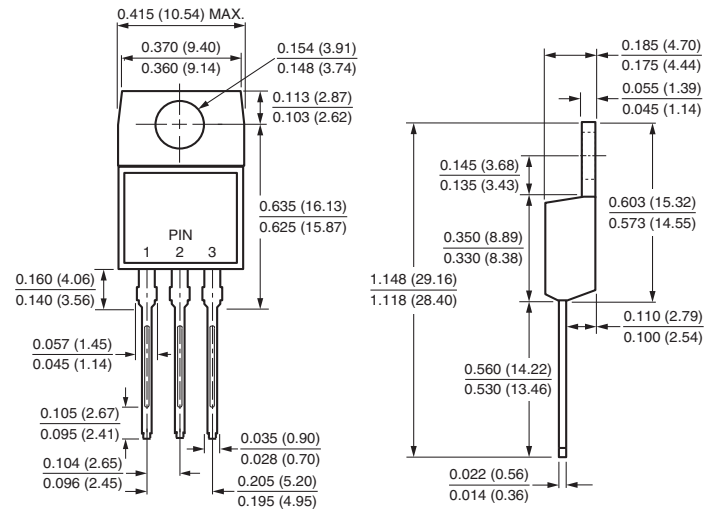
(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)**Current Derating, Case****Maximum Repetitive Surge Current****Typical Forward Voltage****Typical Reverse Current****Typical Junction Capacitance**

PACKAGE OUTLINE

TO-220AB



ITO-220AB

